ABSTRACT OF THE DISCLOSURE

A semiconductor substrate comprises a porous semiconductor having a porous layer with an impurity concentration distribution varying in the depth direction. Alternatively, the semiconductor substrate comprises a porous layer comprising a porous semiconductor containing an impurity with a content of 1×10^{18} cm^{-3} or more, or comprises a porous layer provided by pore formation in an epitaxial growth layer. A thin-film semiconductive member is formed on one surface of a supporting substrate with a porous layer provided having the above-mentioned configuration therebetween, and separated from the supporting substrate by cleavage in the porous layer. In a method for making a semiconductor substrate, a variant impurity layer with an impurity concentration varying in the depth direction is formed on one surface of a supporting substrate. Next, the variant impurity layer is converted into a porous layer having a variant porosity in the depth direction. In a method for making thin-film semiconductive member, a semiconductive thin film is formed and is separated from the supporting substrate by cleavage in the porous phase, in addition to the method for making the semiconductor substrate.